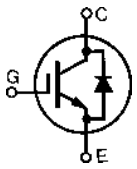
IXYS

IGBT with Diode

IXSK 50N60BU1
IXSX 50N60BU1

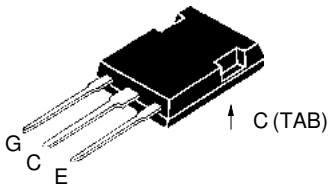
V_{CES} = 600 V
I_{C25} = 75 A
$V_{CE(sat)}$ = 2.5 V

Short Circuit SOA Capability

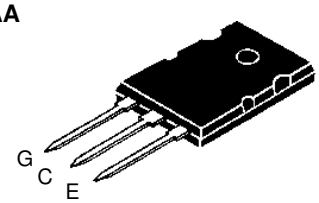


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C, limited by leads	75	A
I_{C90}	T_C = 90°C	50	A
I_{CM}	T_C = 25°C, 1 ms	200	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 22 Ω Clamped inductive load, L = 30 μH	I_{CM} = 100 @ 0.8 V_{CES}	A
t_{SC} **(SCSOA)**	V_{GE} = 15 V, V_{CE} = 360 V, T_J = 125°C R_G = 22 Ω, non repetitive	10	μs
P_C	T_C = 25°C	300	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting torque	0.9/6	Nm/lb.in.
Weight		10	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C

PLUS247 (IXSX)



TO-264 AA (IXSK)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-264 AA, and hole-less TO-247 package for clip mounting
- Guaranteed Short Circuit SOA capability
- High frequency IGBT and anti-parallel FRED in one package
- Latest generation HDMOS™ process
- Low $V_{CE(sat)}$
  - for minimum on-state conduction losses
- MOS Gate turn-on
  - drive simplicity
- Fast Recovery Epitaxial Diode (FRED)
  - soft recovery with low I_{RM}

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Space savings (two devices in one package)
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost

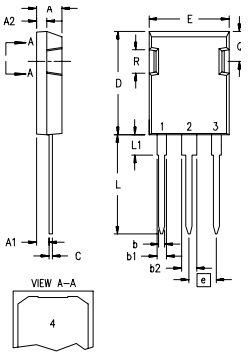
Symbol	Test Conditions		Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 3 mA, V_{GE} = 0 V		600			V
$V_{GE(th)}$	I_C = 4 mA, V_{CE} = V_{GE}		4		8	V
I_{CES}	V_{CE} = 0.8 • V_{CES} V_{GE} = 0 V	T_J = 25°C T_J = 125°C			325 17	μA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V				±100	nA
$V_{CE(sat)}$	I_C = I_{C90}; V_{GE} = 15 V,			2.2	2.5	V

Symbol	Test Conditions (T$_J$ = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
g_{fs}	$I_C = I_{C90}$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	20	23		S
$I_{C(on)}$	V_{GE} = 15 V, V_{CE} = 10 V		160		A
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		3850		pF
C_{oes}			440		pF
C_{res}			50		pF
Q_g	$I_C = I_{C90}$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		167		nC
Q_{ge}			45		nC
Q_{gc}			88		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		70		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH,		70		ns
$t_{d(off)}$	V_{CE} = 0.8 V_{CES}, R_G = 2.7 Ω		150	300	ns
t_{fi}	Remarks: Switching times may increase		150	300	ns
E_{off}	for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		3.3	6.0	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		70		ns
t_{ri}	$I_C = I_{C90}$, V_{GE} = 15 V, L = 100 µH		70		ns
E_{on}	V_{CE} = 0.8 V_{CES}, R_G = 2.7 Ω		2.5		mJ
$t_{d(off)}$	Remarks: Switching times may increase		230		ns
t_{fi}	for V_{CE} (Clamp) > 0.8 • V_{CES}, higher T_J or increased R_G		230		ns
E_{off}			4.8		mJ
R_{thJC}				0.42	K/W
R_{thCK}			0.15		K/W

Reverse Diode (FRED)

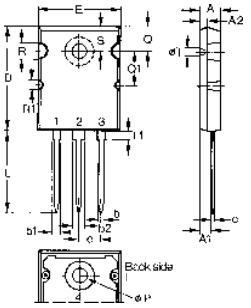
Symbol	Test Conditions (T$_J$ = 25°C, unless otherwise specified)	Characteristic Values min.	typ.	max.	
V_F	$I_F = I_{C90}$, V_{GE} = 0 V, Pulse test, t ≤ 300 µs, duty cycle d ≤ 2 %			1.8	V
I_{RM}	$I_F = I_{C90}$, V_{GE} = 0 V, -di$_F$/dt = 480 A/µs		19	33	A
t_{rr}	V_R = 360 V T_J = 125°C		175		ns
	I_F = 1 A; -di/dt = 200 A/µs; V_R = 30 V T_J = 25°C		35	50	ns
R_{thJC}				0.75	K/W

PLUS247™ (IXSX)



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

TO-264 AA Outline



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

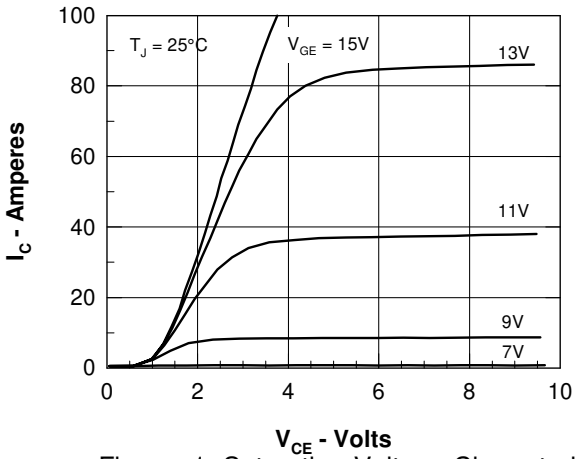


Figure 1. Saturation Voltage Characteristics

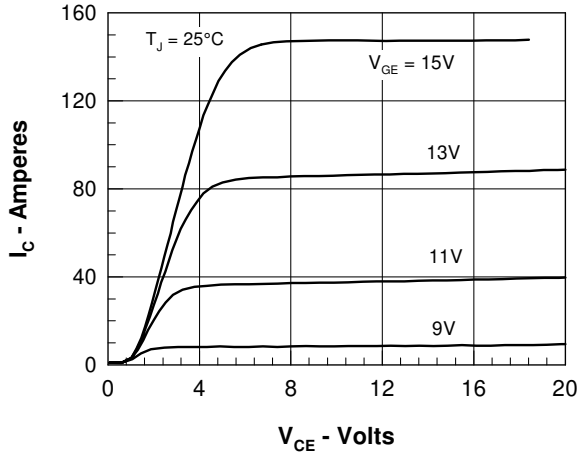


Figure 2. Extended Output Characteristics

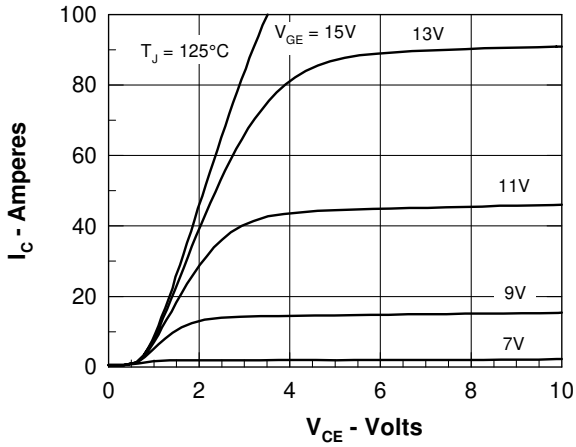


Figure 3. Saturation Voltage Characteristics

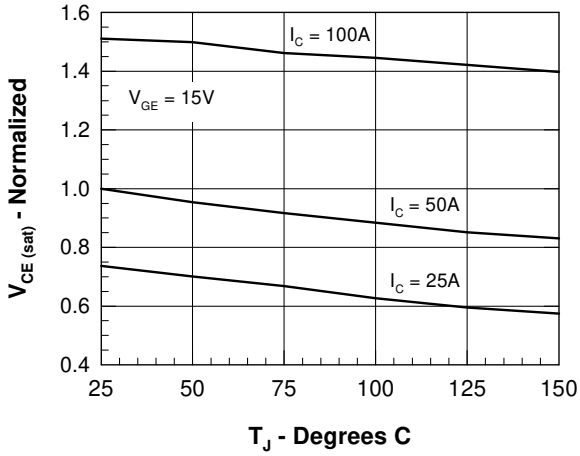


Figure 4. Temperature Dependence of $V_{CE(sat)}$

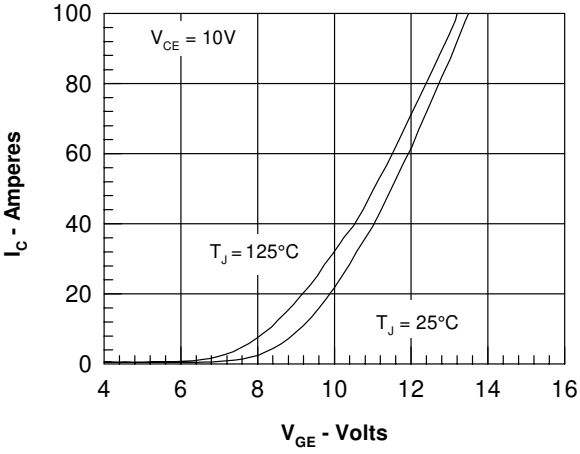


Figure 5. Admittance Curves

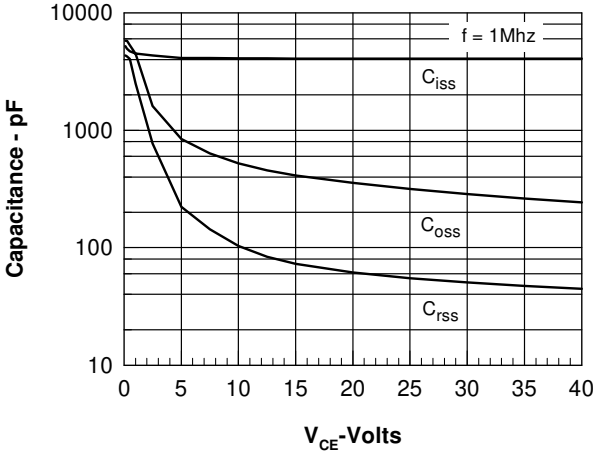


Figure 6. Capacitance Curves

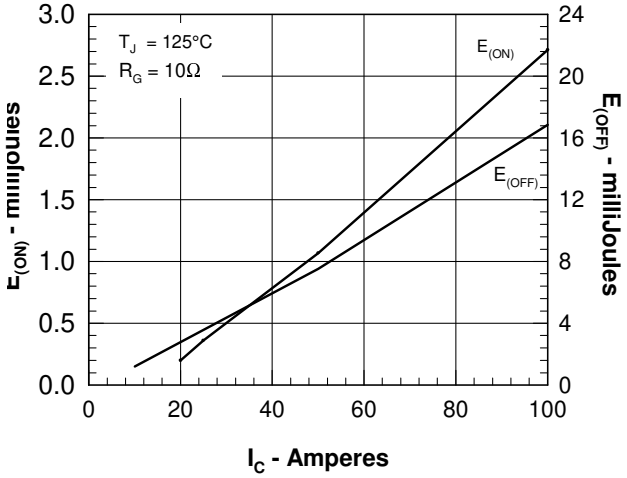


Figure 7. Dependence of E_{ON} and E_{OFF} on I_C.

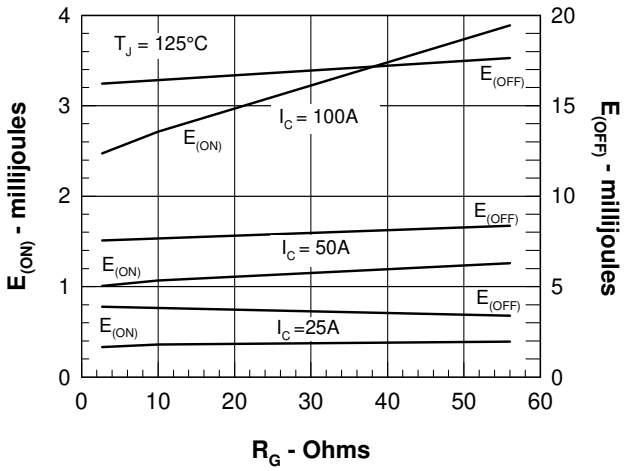


Figure 8. Dependence of E_{ON} and E_{OFF} on R_G.

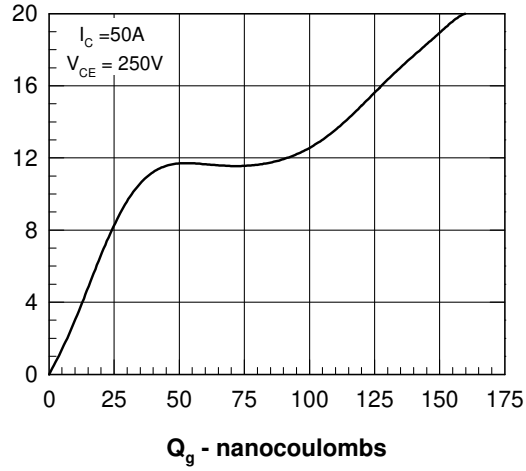


Figure 9. Gate Charge

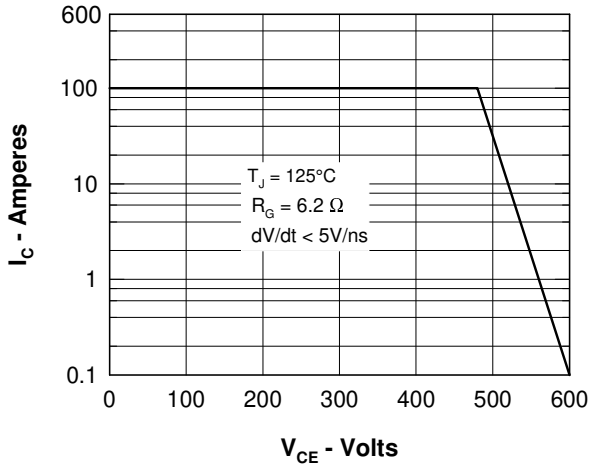


Figure 10. Turn-off Safe Operating Area

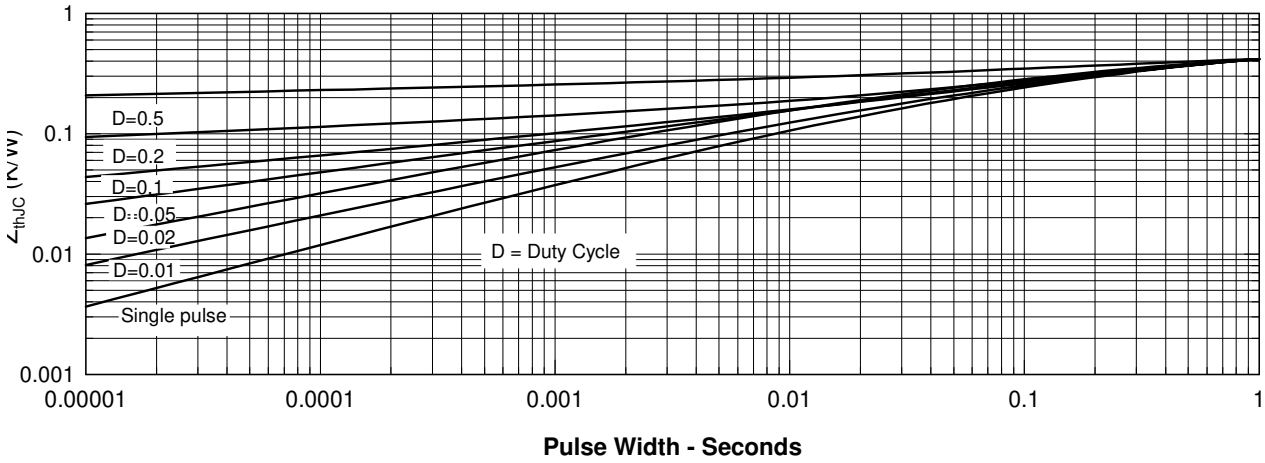


Figure 11. Transient Thermal Resistance

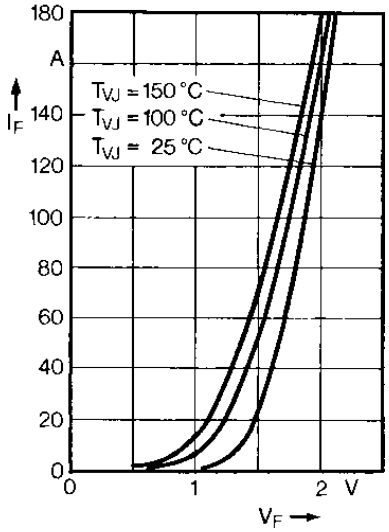


Fig. 12 Forward current versus voltage drop.

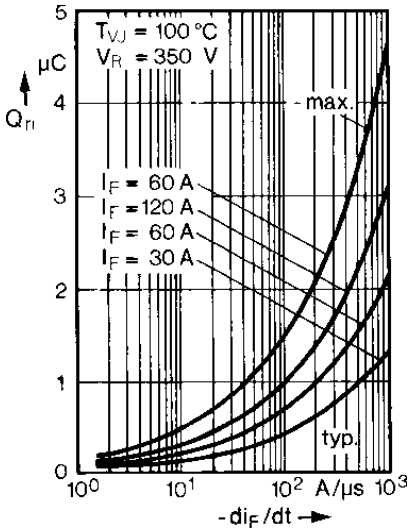


Fig. 13 Recovery charge versus $-di_F/dt$.

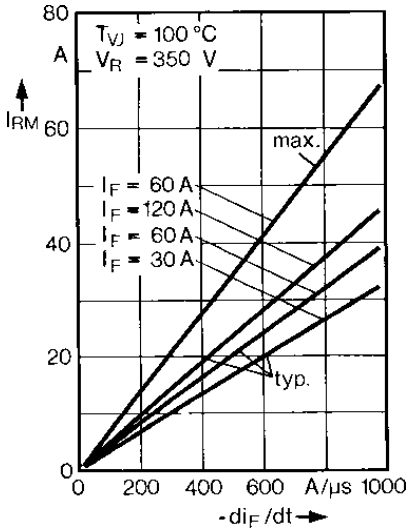


Fig. 14 Peak reverse current versus $-di_F/dt$.

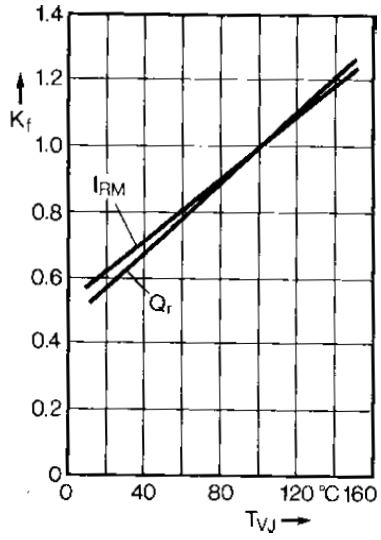


Fig. 15. Dynamic parameters versus junction temperature.

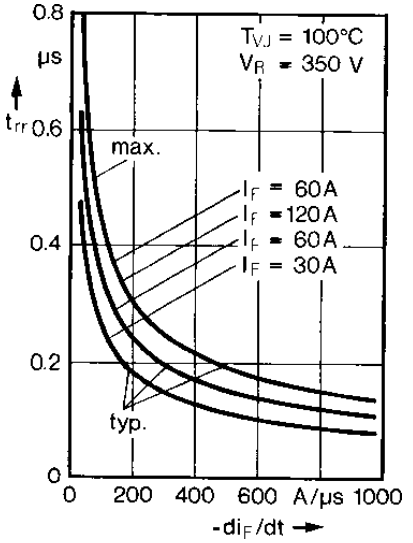


Fig. 16 Recovery time versus $-di_F/dt$.

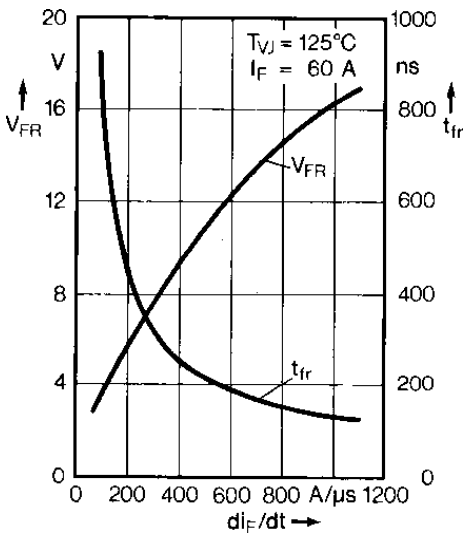


Fig. 17 Peak forward voltage vs. di_F/dt.

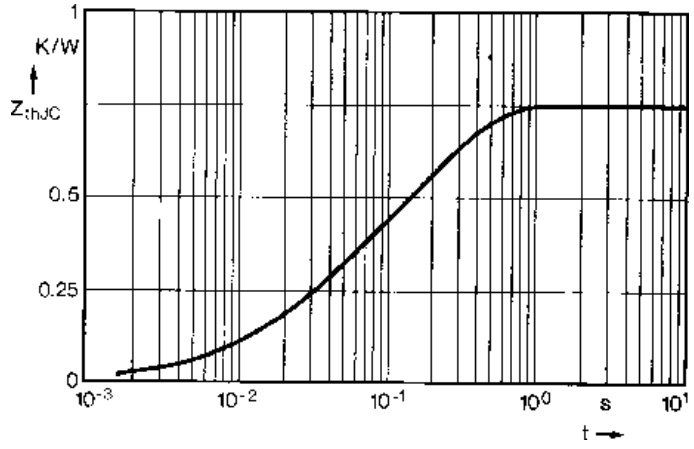


Fig. 18 Transient thermal impedance junction to case.

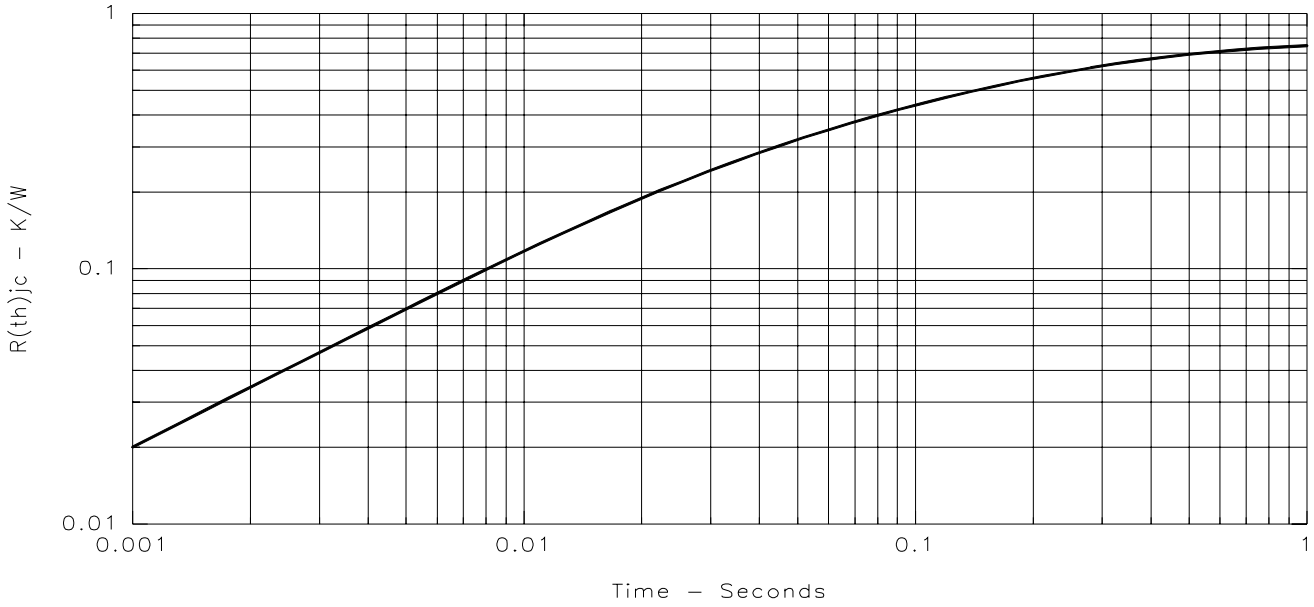


Fig. 18. Diode transient thermal resistance junction-to-case.